

Title (en)

HIGH VOLTAGE COMPONENT AND METHOD FOR MAKING SAME

Title (de)

HOCHSPANNUNGSBAUELEMENT UND VERFAHREN ZU SEINER HERSTELLUNG

Title (fr)

COMPOSANT HAUTE TENSION ET SON PROCEDE DE PRODUCTION

Publication

**EP 1008182 A1 20000614 (DE)**

Application

**EP 98914831 A 19980228**

Priority

- DE 9800597 W 19980228
- DE 19735542 A 19970816

Abstract (en)

[origin: DE19735542A1] A high voltage component has a self-supporting n-doped semiconductor wafer with two or more series-connected sub-components, at least one of which has a p-region extending from the front face to the back face of the wafer. An Independent claim is also included for production of the above component by forming uniformly spaced-apart, parallel, stripe-like p-regions in a lightly n-doped semiconductor component, the p-regions extending from the front face to the back face of the wafer and dividing the wafer into parallel lightly n-doped regions.

IPC 1-7

**H01L 27/08**; H01L 27/144; H01L 29/06; H01L 21/761; H01L 29/87; H01L 31/111

IPC 8 full level

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CPC (source: EP US)

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Citation (search report)

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